

Silicon NPN Power Transistors

2N6356

DESCRIPTION

- With TO-3 package
- High DC current gain
- DARLINGTON

APPLICATIONS

- For general-purpose amplifier and low-frequency switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

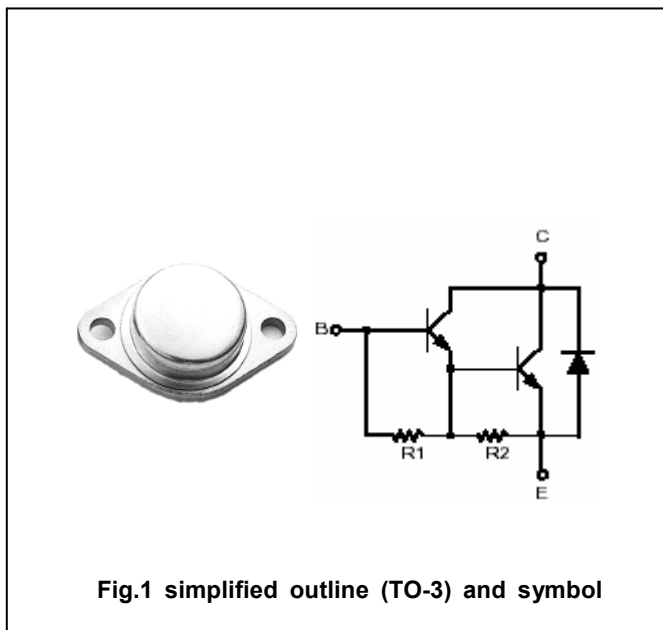


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	50	V
V _{CEO}	Collector-emitter voltage	Open base	40	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		20	A
I _B	Base current		0.5	A
P _D	Total Power Dissipation	T _C =25□	150	W
T _j	Junction temperature		200	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.09	□/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =0.2A ; I _B =0	40			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =10A ; I _B =40mA			2.0	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =20A ; I _B =1A			4.0	V
V _{BE sat}	Base-emitter saturation voltage	I _C =20A ; I _B =1A			4.0	V
V _{BE}	Base-emitter on voltage	I _C =10A ; V _{CE} =4V			2.8	V
I _{CEO}	Collector cut-off current	V _{CE} =40V; I _B =0			1.0	mA
I _{CBO}	Collector cut-off current	V _{CB} =50V; I _E =0			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			5.0	mA
h _{FE-1}	DC current gain	I _C =4A ; V _{CE} =5V	1500		20000	
h _{FE-2}	DC current gain	I _C =20A ; V _{CE} =5V	100			

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.10mm)